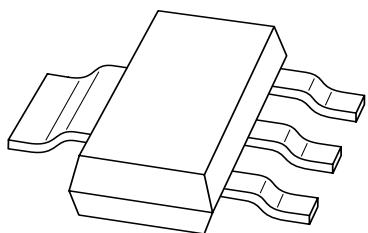


DATA SHEET



BCP54; BCP55; BCP56 NPN medium power transistors

Product specification
Supersedes data of 2001 Oct 10

2003 Feb 06

NPN medium power transistors

BCP54; BCP55; BCP56

FEATURES

- High collector current
- 1.3 W power dissipation.

APPLICATIONS

- General purpose medium power DC applications
- Low and medium frequency AC applications
- Peripheral drivers
- Linear voltage regulators and battery chargers.

DESCRIPTION

NPN medium power transistor in a SOT223 plastic package. PNP complements: BCP51, BCP52 and BCP53.

PINNING

PIN	DESCRIPTION
1	base
2, 4	collector
3	emitter

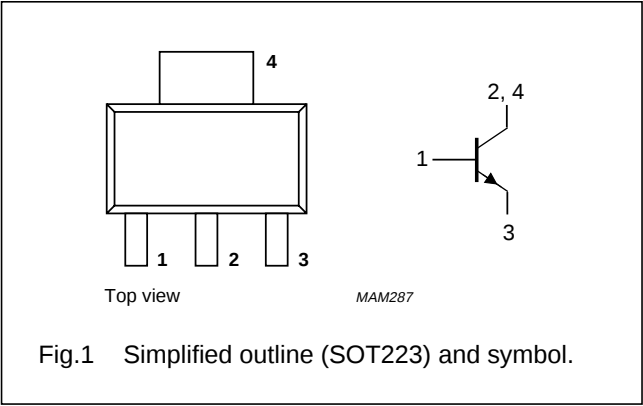


Fig.1 Simplified outline (SOT223) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	80	V
I_C	collector current (DC)	1	A
I_{CM}	peak collector current	1.5	A

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BCP54		–	45	V
	BCP55		–	60	V
	BCP56		–	100	V
V _{CEO}	collector-emitter voltage	open base			
	BCP54		–	45	V
	BCP55		–	60	V
	BCP56		–	80	V
V _{EBO}	emitter-base voltage	open collector	–	5	V
I _C	collector current (DC)		–	1	A
I _{CM}	peak collector current		–	1.5	A
I _{BM}	peak base current		–	0.2	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	1.33	W
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Device mounted on printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see “*Thermal considerations for SOT223 in the General Part of associated Handbook*”.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	94	K/W
R _{th j-s}	thermal resistance from junction to soldering point		13	K/W

Note

1. Device mounted on printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see “*Thermal considerations for SOT223 in the General Part of associated Handbook*”.

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CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	–	–	100	nA
		$I_E = 0; V_{CB} = 30\text{ V}; T_j = 125\text{ }^{\circ}\text{C}$	–	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	–	100	nA
h_{FE}	DC current gain	$I_C = 5\text{ mA}; V_{CE} = 2\text{ V}$	63	–	–	
		$I_C = 150\text{ mA}; V_{CE} = 2\text{ V}$	63	–	250	
		$I_C = 500\text{ mA}; V_{CE} = 2\text{ V}$	40	–	–	
h_{FE}	DC current gain BCP54-10; BCP55-10; BCP56-10 BCP54-16; BCP55-16; BCP56-16	$I_C = 150\text{ mA}; V_{CE} = 2\text{ V}$		–		
			63	–	160	
			100	–	250	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 0.5\text{ A}; I_B = 50\text{ mA}$	–	–	500	mV
V_{BE}	base-emitter voltage	$I_C = 0.5\text{ A}; V_{CE} = 2\text{ V}$	–	–	1	V
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	–	130	–	MHz
$\frac{h_{FE1}}{h_{FE2}}$	DC current gain ratio of the complementary pairs	$ I_C = 150\text{ mA}; V_{CE} = 2\text{ V}$	–	–	1.6	

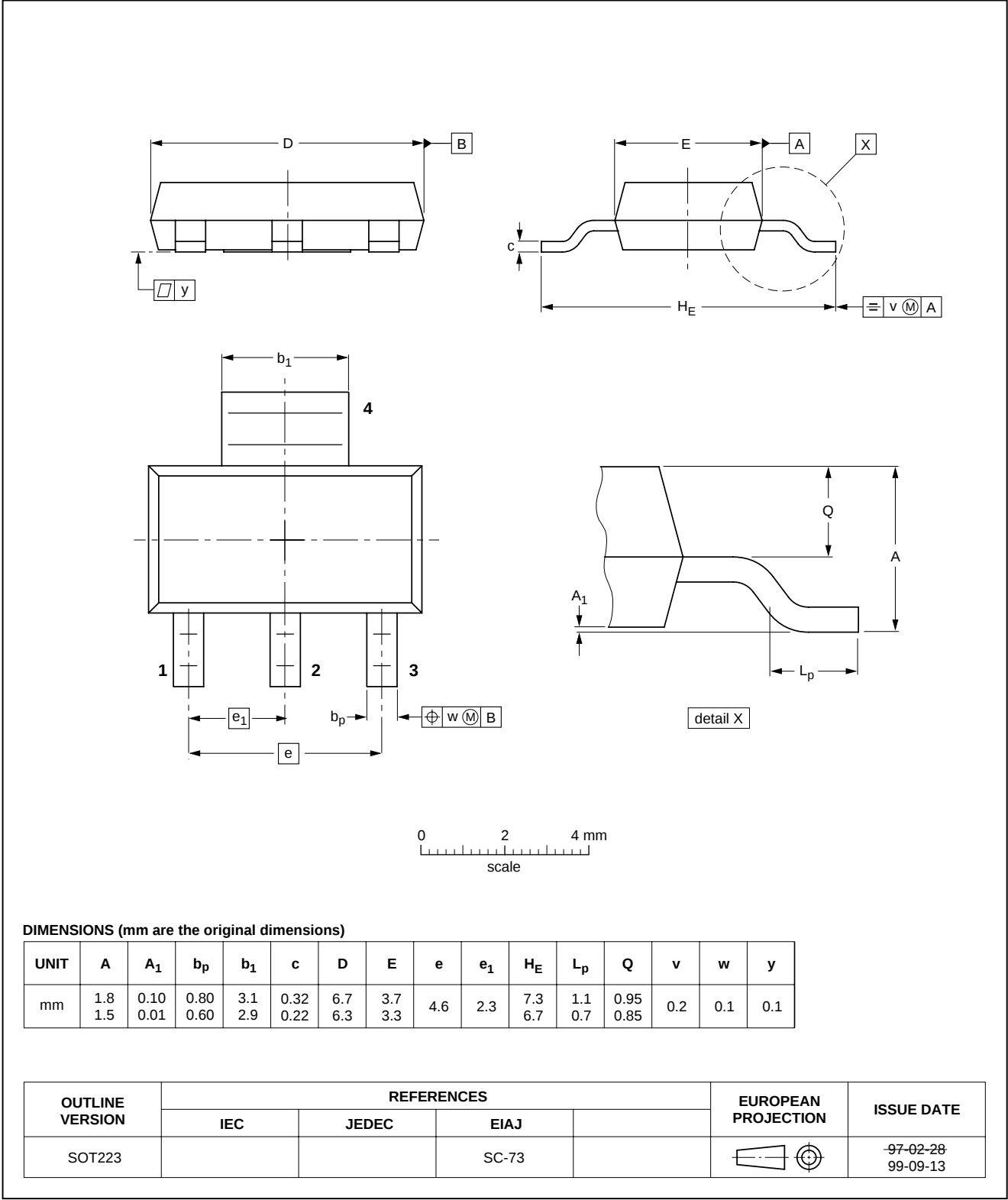
NPN medium power transistors

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PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



NPN medium power transistors

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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NOTES

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